

MSE/EE 5201 Phys of Semiconductor Devices HW# 5 ANSWERS

3.11. (a) $\sigma = q(n\mu_n + p\mu_p) = q(n\mu_n + \frac{n_i^2}{n}\mu_p) = \sigma(n) \dots (1)$

$$\frac{d\sigma}{dn} = q(\mu_n - \frac{n_i^2}{n^2}\mu_p) = 0 \Rightarrow n^* = n_i \left(\frac{\mu_p}{\mu_n}\right)^{1/2} \dots (2)$$

i.e. $\sigma_{min} = \sigma|_{n=n^*} \dots (3)$

(b) $\sigma_{min} = q(n^*\mu_n + \frac{n_i^2}{n^*}\mu_p)$
 $= q\left(n_i \left(\frac{\mu_p}{\mu_n}\right)^{1/2} \mu_n + \frac{n_i^2}{n_i \left(\frac{\mu_p}{\mu_n}\right)^{1/2}} \mu_p\right)$

$$\sigma_{min} = 2q n_i \sqrt{\mu_p \mu_n} \dots (4)$$

(c) $T = 300^\circ K$ $n_i = 1.5 \times 10^{10} \text{ cm}^{-3}$ for Si
 $\mu_n = 1350 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$ $\mu_p = 480 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$

$$\sigma_{min} = 2 \times 1.6 \times 10^{-19} \text{ C} \times 1.5 \times 10^{10} \text{ cm}^{-3} \times \sqrt{1350 \times 480} \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1}$$

$$\sigma_{min} = 3.86 \times 10^{-6} (\Omega \cdot \text{cm})^{-1} \dots (5)$$

while $\sigma_{intrinsic} = q n_i (\mu_n + \mu_p)$
 $= 1.6 \times 10^{-19} \times 1.5 \times 10^{10} \times (1350 + 480)$

$$\sigma_{intrinsic} = 4.39 \times 10^{-6} (\Omega \cdot \text{cm})^{-1} \dots (6)$$

$$\sigma_{min} < \sigma_{intrinsic} \dots (7)$$

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3.12. (a) $N_d = 10^{17} \text{ cm}^{-3}$ $\mu_n \cong 700 \text{ cm}^2 \cdot \text{V}^{-1} \text{ s}^{-1}$

$$I = JA = 5 \cdot \frac{V}{L} A = q(n\mu_n + p\mu_p) \frac{V}{L} A \quad \dots (1)$$

$$n \approx N_d = 10^{17} \Rightarrow p \quad \dots (2)$$

so, $I = qN_d\mu_n \cdot \frac{V}{L} A \quad \dots (3)$

~~Ohm's Law~~

$$I = 1.6 \times 10^{-19} \text{ C} \times 10^{17} \text{ cm}^{-3} \times 700 \text{ cm}^2 \cdot \text{V}^{-1} \text{ s}^{-1} \times \frac{10 \text{ V}}{0.1 \text{ cm}} \times 100 \mu\text{m}^2 \times 10^{-8} \text{ cm}^2 / \mu\text{m}^2$$

$$I = 1.12 \times 10^{-3} \text{ A} = 1.12 \text{ mA} \quad \dots (4)$$

(b) $L = 1 \mu\text{m} = 10^{-4} \text{ cm}$

$$I = 1.12 \times 10^{-3} \times \frac{0.1}{10^{-4}} = 1.12 \text{ A} \quad \dots (5)$$

(c) $L = 1 \mu\text{m} = 10^{-4} \text{ cm}$

$$t = \frac{L}{v} = \frac{L}{\mu_n \cdot \frac{V}{L}} = \frac{L^2}{\mu_n \cdot V}$$

$$t = \frac{(10^{-4})^2 \text{ cm}^2}{1350 \text{ cm}^2 \cdot \text{V}^{-1} \cdot \text{s}^{-1} \times 10 \text{ V}} = 7.4 \times 10^{-10} \text{ s} \quad \dots (6)$$

At $E = 10^5 \text{ V/cm}$ $v = v_{\text{saturation}} = 10^7 \text{ cm/s}$

$$t = \frac{10^{-4} \text{ cm}}{10^7 \text{ cm/s}} = 10^{-11} \text{ s} \quad \dots (7)$$

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4.7. $n = n_0 + \delta n \approx N_d + \tau_n \cdot G = 10^{15} + 10^{-6} \times 10^{21} = 2 \times 10^{15} \text{ cm}^{-3}$

$P = P_0 + \delta p \approx \tau_p \cdot G = 10^{-6} \times 10^{21} = 10^{15} \text{ cm}^{-3}$

Since $P_0 = \frac{n_i^2}{n_0} = \frac{(1.5 \times 10^{10})^2}{10^{15}} = 2.25 \times 10^5 \ll 10^{15}$

$n = n_i \exp[(E_{Fn} - E_i)/kT] \Rightarrow E_{Fn} - E_i = kT \ln\left(\frac{n}{n_i}\right)$

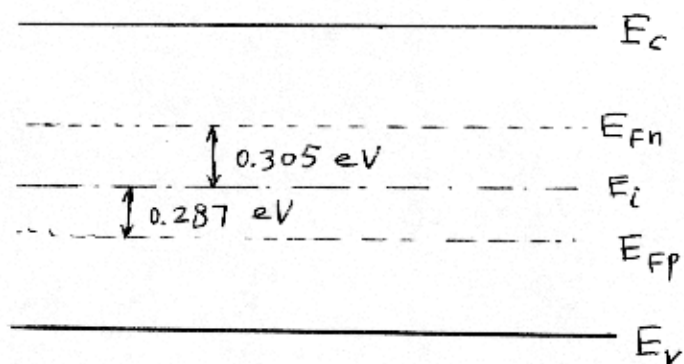
$p = n_i \exp[(E_i - E_{Fp})/kT] \Rightarrow E_i - E_{Fp} = kT \ln\left(\frac{p}{n_i}\right)$

At 300°K , $kT \approx 0.0258 \text{ eV}$

$E_{Fn} - E_i = 0.0258 \times \ln \frac{2 \times 10^{15}}{1.5 \times 10^{10}} = 0.305 \text{ eV}$

$E_i - E_{Fp} = 0.0258 \times \ln \frac{10^{15}}{1.5 \times 10^{10}} = 0.287 \text{ eV}$

$\therefore E_{Fn} - E_{Fp} = 0.305 + 0.287 = 0.592 \text{ eV}$



4.8. (a) without generation $n \cong N_d = 10^{16} \text{ cm}^{-3}$ $p \ll n$

$$I = \sigma \cdot \frac{V}{L} A = q(n\mu_n + p\mu_p) \cdot \frac{V}{L} A \approx qn\mu_n \cdot \frac{V}{L} A$$

$$I = 1.6 \times 10^{-19} \times 10^{16} \times 1100 \times \frac{10}{2} \times 0.05 = 0.44 \text{ A}$$

(b) Consider EHP generation

$$n = N_d + \tau_n \cdot G = 10^{16} + 10^{-4} \times 10^{20} = 2 \times 10^{16} \text{ cm}^{-3}$$

$$p = \frac{n_i^2}{N_d} + \tau_p \cdot G \approx 10^{-4} \times 10^{20} = 10^{16} \text{ cm}^{-3}$$

$$I = q(n\mu_n + p\mu_p) \cdot \frac{V}{L} A$$

$$I = 1.6 \times 10^{-19} \times (2 \times 10^{16} \times 1100 + 10^{16} \times 500) \times \frac{10}{2} \times 0.05 = 1.08 \text{ A}$$

(c) With EHP generation at $V = 10^5$ Volts

$$V/L = 10^5 / 2 \text{ cm} = 5 \times 10^4 \text{ V/cm}$$

From Figure, get $v_d(\text{electron}) \cong 10^7 \text{ cm/s}$

Assume $v_d(\text{hole}) \cong 10^7 \text{ cm/s}$

Then $I = q(n+p)v_d \cdot A$

$$I = 1.6 \times 10^{-19} \times (2 \times 10^{16} + 10^{16}) \times 10^7 \times 0.05$$

$$I = 2400 \text{ A}$$